

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
21 July 2005 (21.07.2005)

PCT

(10) International Publication Number  
**WO 2005/067035 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 21/8242**

(21) International Application Number:

PCT/US2003/038559

(22) International Filing Date: 4 December 2003 (04.12.2003)

(25) Filing Language:

English

(26) Publication Language:

English

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (*regional*): ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

**Declaration under Rule 4.17:**

— of inventorship (Rule 4.17(iv)) for US only

**Published:**

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD FOR FORMING NON-AMORPHOUS, ULTRA-THIN SEMICONDUCTOR DEVICES USING SACRIFICIAL IMPLANTATION LAYER

(57) Abstract: A method for forming a semiconductor device includes defining a sacrificial layer (108) over a single crystalline substrate (106). The sacrificial layer (108) is implanted with a dopant species in a manner that prevents the single crystalline substrate (106) from becoming substantially amorphized. The sacrificial layer (108) is annealed so as to drive said dopant species from said sacrificial layer (108) into said single crystalline substrate (106).



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